

Shuichi Noda

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Atomic layer defect-free etching for germanium using HBr neutral beam. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, 051001.	2.1	4
2	Atomic layer germanium etching for 3D Fin-FET using chlorine neutral beam. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	2.1	15
3	Structural optimization and quantum size effect of Si-nanocrystals in SiC interlayer fabricated with bio-template. Materials Research Express, 2019, 6, 065059.	1.6	8
4	High-Performance GaN MOSHEMTs Fabricated With ALD Al ₂ O ₃ Dielectric and NBE Gate Recess Technology for High Frequency Power Applications. IEEE Electron Device Letters, 2017, 38, 771-774.	3.9	21
5	Spin relaxation in Si nanoclusters embedded in free-standing SiGe nanocolumns. Applied Physics Letters, 2017, 110, 203103.	3.3	2
6	Corrections to "AlGaIn/GaN HEMTs With Damage-Free Neutral Beam Etched Gate Recess for High-Performance Millimeter-Wave Applications" [Nov 16 1395-1398]. IEEE Electron Device Letters, 2017, 38, 149-149.	3.9	0
7	Impacts of plasma-induced damage due to UV light irradiation during etching on Ge fin fabrication and device performance of Ge fin field-effect transistors. Applied Physics Express, 2017, 10, 026501.	2.4	33
8	Defect-free germanium etching for 3D Fin MOSFET using neutral beam etching. , 2016, , .		1
9	Enhancement-mode AlGaIn/GaN MIS-HEMTs with low threshold voltage hysteresis using damage-free neutral beam etched gate recess. , 2016, , .		1
10	High performance complementary Ge peaking FinFETs by room temperature neutral beam oxidation for sub-7 nm technology node applications. , 2016, , .		12
11	AlGaIn/GaN HEMTs With Damage-Free Neutral Beam Etched Gate Recess for High-Performance Millimeter-Wave Applications. IEEE Electron Device Letters, 2016, 37, 1395-1398.	3.9	16
12	Defect-free fabrication of nano-disk and nano-wire by fusion of bio-template and neutral beam etching. Proceedings of SPIE, 2016, , .	0.8	0
13	Highly oriented polycrystalline Cu ₂ O film formation using RF magnetron sputtering deposition for solar cells. , 2014, , .		3
14	Cu ₂ O/ZnO Heterojunction Solar Cells Fabricated by Magnetron-Sputter Deposition Method Films Using Sintered Ceramics Targets. Journal of Physics: Conference Series, 2013, 433, 012027.	0.4	29
15	Fabrication of FinFETs by Damage-Free Neutral-Beam Etching Technology. IEEE Transactions on Electron Devices, 2006, 53, 1826-1833.	3.0	37
16	New Fabrication Technology of Fin Field Effect Transistors Using Neutral-Beam Etching. Japanese Journal of Applied Physics, 2006, 45, 5513-5516.	1.5	5
17	Fabrication of a Vertical-Channel Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistor Using a Neutral Beam Etching. Japanese Journal of Applied Physics, 2006, 45, L279-L281.	1.5	9
18	Damage-free metal-oxide-semiconductor gate electrode patterning on thin HfSiON film using neutral beam etching. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 1414-1420.	2.1	10

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19	Highly anisotropic gate electrode patterning in neutral beam etching using F ₂ gas chemistry. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2063.	1.6	10
20	50 nm gate electrode patterning using a neutral-beam etching system. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 1506-1512.	2.1	60
21	Investigation of ion transportation in high-aspect-ratio holes from fluorocarbon plasma for SiO ₂ etching. Thin Solid Films, 2000, 374, 181-189.	1.8	15
22	Volume/surface effects on electron energy and dissociation reactions in large-volume plasma reactors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1520-1525.	2.1	5
23	Mechanism of C ₄ F ₈ dissociation in parallel-plate-type plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 2557-2571.	2.1	49
24	Characterization of 100 MHz inductively coupled plasma (ICP) by comparison with 13.56 MHz ICP. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1514-1519.	2.1	16
25	Mechanism of Radical Control in Capacitive RF Plasma for ULSI Processing. Japanese Journal of Applied Physics, 1998, 37, 2394-2399.	1.5	59
26	Plasma-Wall Interactions in Dual Frequency Narrow-Gap Reactive Ion Etching System. Japanese Journal of Applied Physics, 1998, 37, 6899-6905.	1.5	14
27	Monitoring of Electron Energy Distribution Change from Optical Emission for Nonmagnetic Ultrahigh-Frequency Plasma. Japanese Journal of Applied Physics, 1998, 37, 2400-2405.	1.5	4
28	Simulation of x-ray mask displacement by absorber and membrane stress. , 1996, 2793, 211.		0
29	X-Ray Mask Distortion Induced in Back-Etching Preceding Subtractive Fabrication: Resist and Absorber Stress Effect. Japanese Journal of Applied Physics, 1996, 35, 2845-2850.	1.5	10
30	High-precision EB technology with thin EB resist and distortion-free mask holder for x-ray mask fabrication. , 1995, 2512, 142.		2
31	SiC/SiN Multilayer Membrane for X-Ray Mask Deposited by Low Pressure Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1995, 34, 6701.	1.5	1
32	SiC/SiN Multilayer Membrane for X-Ray Mask Deposited by Low Pressure Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1995, 34, 6701-6708.	1.5	0
33	Fabrication of reliable x-ray mask using high-temperature deposited SiN membrane by low-pressure chemical vapor deposition system. , 1994, 2254, 304.		1
34	Improvement in Radiation Stability of SiN X-Ray Mask Membranes. Japanese Journal of Applied Physics, 1993, 32, 5941-5946.	1.5	5
35	Effect of synchrotron radiation on electrical characteristics of SiO _x N _y thin films formed by rapid thermal processing in a N ₂ O ambient. Applied Physics Letters, 1993, 63, 3364-3366.	3.3	6
36	MOS Gate Etching Using an Advanced Magnetron Etching System. Japanese Journal of Applied Physics, 1989, 28, 2362-2367.	1.5	1